L Number	Hits	Search Text	DB	Time stamp	1
-	25			42006606797214007	"47
•			US-PGPUB		
-	13	(HEMT or (High near Electron near Mobility	USPAT;	2004/06/04 11:51	
		near Transistor)) and (AlGaN and SiN and	US-PGPUB;		
		ohmic)	EPO; JPO;		
			DERWENT;	1	
			IBM TDB	1	
_	3938	(HEMT or (High near Electron near Mobility	USPAT;	2004/06/04 11:51	
		near Transistor))	US-PGPUB;		
	1		EPO; JPO;		
			DERWENT;		
			IBM TDB		
-	142		USPAT;	2004/06/04 11:52	
		Mobility near Transistor))) and (carbide)	US-PGPUB;		
			EPO; JPO;		
	I		DERWENT;		
İ	I		IBM TDB		i
_	259	((HEMT or (High near Electron near	USPAT;	2004/06/07 14:26	ı
	1	Mobility near Transistor))) and (carbide	US-PGPUB;	-101,00,0, 11.20	
		or SiC)	EPO; JPO;		
		·	DERWENT;		
			IBM TDB		
_	2	(AlGaN) near channel and HEMT	USPAT;	2004/06/06 11:36	:
	_		US-PGPUB;	2004/00/00 11:50	
			EPO; JPO;		
	i		DERWENT;		
			IBM TDB	-	
_	335	HEMT and ((lift near off) or "lift-off")	USPAT;	2004/06/07 15:21	
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	2001,00,0, 13.21	
		·	EPO; JPO;		
			DERWENT;		
			IBM TDB		
-	2	HEMT and (conductive near mask)	USPAT;	2004/06/07 15:21	
			US-PGPUB;	=====	
			EPO; JPO;		
1			DERWENT;		
i			IBM TDB	ļ	
-	802	(conductive near mask) and semiconductor	USPAT;	2004/06/07 15:24	
		,	US-PGPUB;	,,	
			EPO; JPO;		
			DERWENT;		
			IBM TDB	]	
-	393	((conductive near mask) and semiconductor	USPAT;	2004/06/07 15:23	
İ		) and transistor	US-PGPUB;		
		·	EPO; JPO;		
			DERWENT;		
			IBM TDB		
_	15	(((aluminum near nitride) or AlN) near	USPAT;	2004/06/07 15:24	
		mask) and semiconductor	US-PGPUB;		
			EPO; JPO;		
	ļ		DERWENT;		
			IBM TDB		
-	2	("6548333").PN.	USPAT;	2004/09/16 15:25	
	-	, ,	US-PGPUB;	2504/05/10 15.25	
	l		EPO; JPO;		
	l		DERWENT;		
			IBM_TDB		